

isc Silicon NPN Darlington Power Transistor

2SD1126

DESCRIPTION

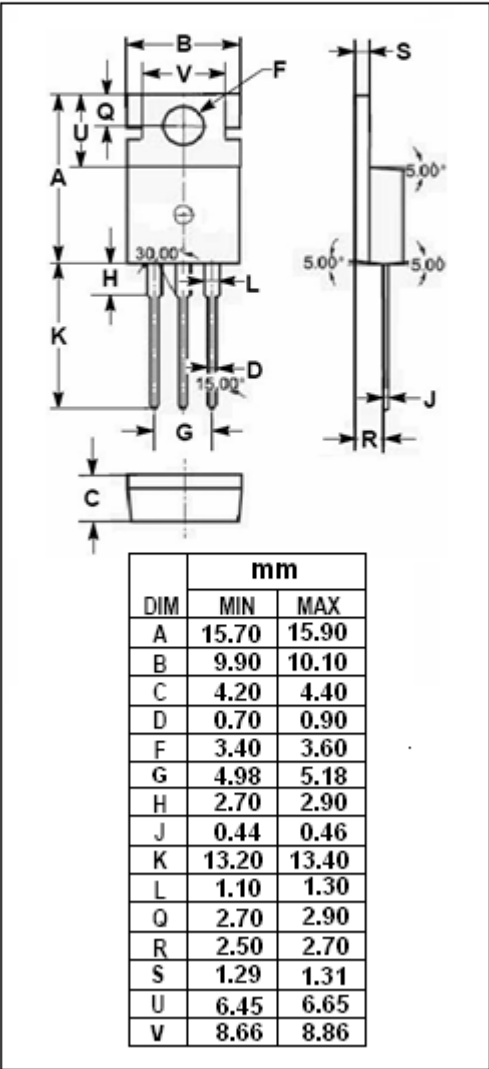
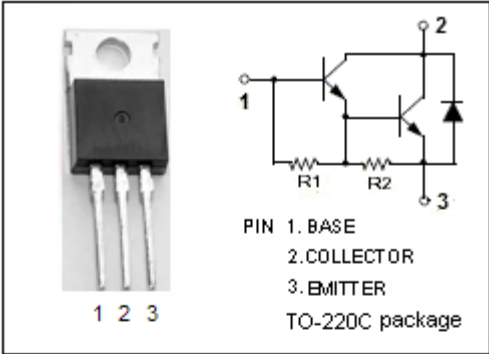
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO}=120V(\text{Min})$
- High DC Current Gain
: $h_{FE}=1000(\text{Min}) @ I_C=5A$
- Low Saturation Voltage

APPLICATIONS

- Designed for power switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	10	A
I_{CP}	Collector Current-Peak	15	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc Silicon NPN Darlington Power Transistor**2SD1126****ELECTRICAL CHARACTERISTICS****T_C=25℃ unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; R _{BE} = ∞	120			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 200mA; I _C = 0	7			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 10mA			1.5	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 10A; I _B = 0.1A			3.0	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 10mA			2.0	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = 10A; I _B = 0.1A			3.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 120V; I _E =0			100	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = 100V; R _{BE} = ∞			10	μ A
h _{FE}	DC Current Gain	I _C = 5A; V _{CE} = 3V	1000		20000	
V _{ECF}	C-E Diode Forward Voltage	I _F = 10A			3.0	V

Switching times

t _{on}	Turn-on Time	I _C = 5A, I _{B1} = -I _{B2} = 10mA		0.8		μ s
t _{off}	Turn-Off Time			8.0		μ s